

LMH6624-MIL Single Ultra-Low-Noise Wideband Operational Amplifier

1 Features

- $V_S = \pm 6\text{ V}$, $T_A = 25^\circ\text{C}$, $A_V = 20$ (Typical Values Unless Specified)
- Gain Bandwidth 1.5 GHz
- Input Voltage Noise $0.92\text{ nV}/\sqrt{\text{Hz}}$
- Input Offset Voltage (Limit Over Temp) $700\text{ }\mu\text{V}$
- Slew Rate $350\text{ V}/\mu\text{s}$
- Slew Rate ($A_V = 10$) $400\text{ V}/\mu\text{s}$
- HD2 at $f = 10\text{ MHz}$, $R_L = 100\text{ }\Omega$ -63 dBc
- HD3 at $f = 10\text{ MHz}$, $R_L = 100\text{ }\Omega$ -80 dBc
- Supply Voltage Range 5 V to 12 V
- Improved Replacement for the CLC425
- Stable for Closed Loop $|A_V| \geq 10$

2 Applications

- Instrumentation Sense Amplifiers
- Ultrasound Preamplifiers
- Magnetic Tape & Disk Preamplifiers
- Wide Band Active Filters
- Professional Audio Systems
- Opto-Electronics
- Medical Diagnostic Systems

3 Description

The LMH6624-MIL device offers wide bandwidth (1.5 GHz) with very-low-input noise ($0.92\text{ nV}/\sqrt{\text{Hz}}$, $2.3\text{ pA}/\sqrt{\text{Hz}}$) and ultra-low DC errors ($100\text{-}\mu\text{V } V_{OS}$, $\pm 0.1\text{-}\mu\text{V}/^\circ\text{C}$ drift) providing very precise operational amplifiers with wide dynamic range. This enables the user to achieve closed-loop gains of greater than 10, in both inverting and non-inverting configurations.

The LMH6624-MIL traditional voltage feedback topology provides the following benefits: balanced inputs, low-offset voltage and offset current, very-low-offset drift, 81-dB open loop gain, 95-dB common-mode rejection ratio, and 88-dB power supply rejection ratio.

The LMH6624-MIL device operates from 5 V to 12 V and is offered in SOT-23-5 and SOIC-8 packages.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
LMH6624-MIL	SOT-23 (5)	2.90 mm × 1.60 mm
	SOIC (8)	4.90 mm × 3.91 mm

(1) For all available packages, see the orderable addendum at the end of the datasheet.

Voltage Noise vs. Frequency

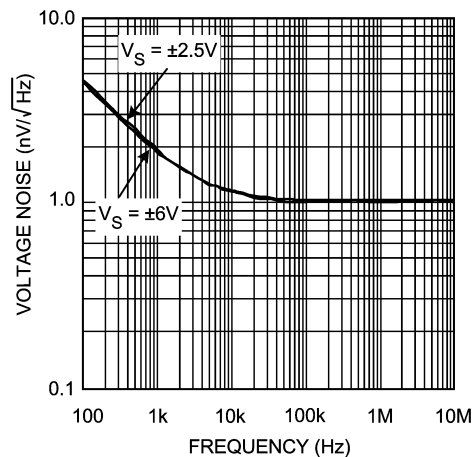


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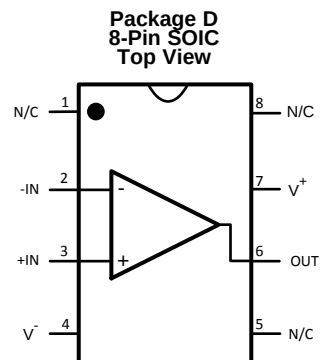
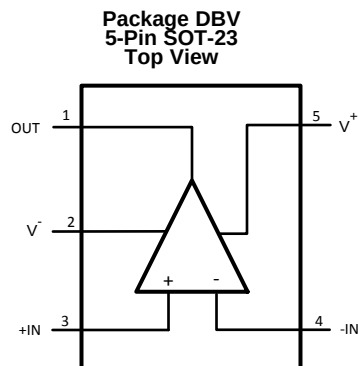
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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

DATE	REVISION	NOTES
June 2017	*	Initial release.

5 Pin Configuration and Functions



Pin Functions

PIN			I/O	DESCRIPTION
NAME	LMH6624-MIL			
	DBV	D		
−IN	4	2	I	Inverting input
+IN	3	3	I	Non-inverting input
N/C	—	1, 5, 8	—	No connection
OUT	1	6	O	Output
V−	2	4	I	Negative supply
V+	5	7	I	Positive supply

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{IN} differential			±1.2	V
Supply voltage (V ⁺ – V [–])			13.2	V
Voltage at input pins			V ⁺ +0.5, V [–] –0.5	V
Input current			±10	mA
Soldering information	Infrared or convection (20 s)		235	°C
	Wave soldering (10 s)		260	°C
Junction temperature ⁽²⁾			150	°C
Storage temperature		–65	150	°C

- (1) Absolute maximum ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not ensured. For ensured specifications and the test conditions, see the Electrical Characteristics.
- (2) Applies to both single-supply and split-supply operation. Continuous short circuit operation at elevated ambient temperature can result in exceeding the maximum allowed junction temperature of 150°C.

6.2 ESD Ratings

	VALUE	UNIT
$V_{(ESD)}$ Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000
	Machine model ⁽²⁾	±200

- (1) Human body model, 1.5 k Ω in series with 100 pF. JEDEC document JEP155 states that 2000-V HBM allows safe manufacturing with a standard ESD control process. Manufacturing with less than 2000-V HBM is possible with the necessary precautions. Pins listed as ±2000 V may actually have higher performance.
- (2) Machine model, 0 Ω in series with 200 pF. JEDEC document JEP157 states that 200-V MM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

	MIN	MAX	UNIT
Operating temperature ⁽²⁾	–40	+125	°C
Operating supply voltage ($V^+ - V^-$)	±2.25	±6.3	V

- (1) Absolute maximum ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not ensured. For ensured specifications and the test conditions, see the Electrical Characteristics.
- (2) Applies to both single-supply and split-supply operation. Continuous short circuit operation at elevated ambient temperature can result in exceeding the maximum allowed junction temperature of 150°C.

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾	LMH6624-MIL		UNIT
	DBV	D	
	5 PINS	8 PINS	
$R_{\theta JA}$ Junction-to-ambient thermal resistance ⁽²⁾	265	166	°C/W

- (1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).
- (2) The maximum power dissipation is a function of $T_{J(MAX)}$, $R_{\theta JA}$, and T_A . The maximum allowable power dissipation at any ambient temperature is $P_D = (T_{J(MAX)} - T_A) / R_{\theta JA}$. All numbers apply for packages soldered directly onto a PC board.

6.5 Electrical Characteristics ± 2.5 V

Unless otherwise specified, all limits ensured at $T_A = 25^\circ\text{C}$, $V^+ = 2.5$ V, $V^- = -2.5$ V, $V_{CM} = 0$ V, $A_V = +20$, $R_F = 500\ \Omega$, $R_L = 100\ \Omega$. See ⁽¹⁾.

PARAMETER		TEST CONDITIONS	MIN ⁽²⁾	TYP ⁽³⁾	MAX ⁽²⁾	UNIT
DYNAMIC PERFORMANCE						
f_{CL}	–3-dB BW	$V_O = 400$ mV _{PP}		90		MHz
SR	Slew rate ⁽⁴⁾	$V_O = 2$ V _{PP} , $A_V = +20$		300		V/ μ s
		$V_O = 2$ V _{PP} , $A_V = +10$		360		
t_r	Rise time	$V_O = 400$ mV Step, 10% to 90%		4.1		ns
t_f	Fall time	$V_O = 400$ mV Step, 10% to 90%		4.1		ns
t_s	Settling time 0.1%	$V_O = 2$ V _{PP} (Step)		20		ns
DISTORTION and NOISE RESPONSE						
e_n	Input referred voltage noise	$f = 1$ MHz		0.92		nV/ $\sqrt{\text{Hz}}$
				1.0		
i_n	Input referred current noise	$f = 1$ MHz		2.3		pA/ $\sqrt{\text{Hz}}$
HD2	2 nd harmonic distortion	$f_C = 10$ MHz, $V_O = 1$ V _{PP} , $R_L = 100\ \Omega$		–60		dBc
HD3	3 rd harmonic distortion	$f_C = 10$ MHz, $V_O = 1$ V _{PP} , $R_L = 100\ \Omega$		–76		dBc
INPUT CHARACTERISTICS						
V_{OS}	Input offset voltage	$V_{CM} = 0$ V	–0.75	–0.25	+0.75	mV
		$-40^\circ\text{C} \leq T_J \leq 125^\circ\text{C}$	–0.95		+0.95	
	Average drift ⁽⁵⁾	$V_{CM} = 0$ V		± 0.25		$\mu\text{V}/^\circ\text{C}$
I_{OS}	Input offset current	$V_{CM} = 0$ V	–1.5	–0.05	+1.5	μA
		$-40^\circ\text{C} \leq T_J \leq 125^\circ\text{C}$	–2.0		+2.0	
	Average drift ⁽⁵⁾	$V_{CM} = 0$ V		2		nA/ $^\circ\text{C}$
I_B	Input bias current	$V_{CM} = 0$ V		13	+20	μA
		$-40^\circ\text{C} \leq T_J \leq 125^\circ\text{C}$			+25	
	Average drift ⁽⁵⁾	$V_{CM} = 0$ V		12		nA/ $^\circ\text{C}$
R_{IN}	Input resistance ⁽⁶⁾	Common Mode		6.6		M Ω
		Differential Mode		4.6		k Ω
C_{IN}	Input capacitance ⁽⁶⁾	Common Mode		0.9		pF
		Differential Mode		2.0		
CMRR	Common-mode rejection ratio	Input referred, $V_{CM} = -0.5$ V to $+1.9$ V		87	90	dB
		Input referred, $V_{CM} = -0.5$ V to $+1.75$ V, $-40^\circ\text{C} \leq T_J \leq 125^\circ\text{C}$		85		

- (1) Electrical table values apply only for factory testing conditions at the temperature indicated. Factory testing conditions result in very limited self-heating of the device such that $T_J = T_A$. No ensured specification of parametric performance is indicated in the electrical tables under conditions of internal self-heating where $T_J > T_A$. Absolute maximum ratings indicate junction temperature limits beyond which the device may be permanently degraded, either mechanically or electrically.
- (2) All limits are specified by testing or statistical analysis.
- (3) Typical Values represent the most likely parametric norm.
- (4) Slew rate is the slowest of the rising and falling slew rates.
- (5) Average drift is determined by dividing the change in parameter at temperature extremes into the total temperature change.
- (6) Simulation results.

Electrical Characteristics ± 2.5 V (continued)

Unless otherwise specified, all limits ensured at $T_A = 25^\circ\text{C}$, $V^+ = 2.5$ V, $V^- = -2.5$ V, $V_{CM} = 0$ V, $A_V = +20$, $R_F = 500\ \Omega$, $R_L = 100\ \Omega$. See ⁽¹⁾.

PARAMETER		TEST CONDITIONS		MIN ⁽²⁾	TYP ⁽³⁾	MAX ⁽²⁾	UNIT
TRANSFER CHARACTERISTICS							
A _{VOL}	Large signal voltage gain	R _L = 100 Ω, V _O = −1 V to +1 V		75	79		dB
			−40°C ≤ T _J ≤ 125°C	70			
OUTPUT CHARACTERISTICS							
V _O	Output swing	R _L = 100 Ω		±1.1	±1.5		V
			−40°C ≤ T _J ≤ 125°C	±1.0			
		No load		±1.4	±1.7		
			−40°C ≤ T _J ≤ 125°C	±1.25			
R _O	Output impedance	f ≤ 100 KHz		10			mΩ
I _{SC}	Output short circuit current	Sourcing to ground ΔV _{IN} = 200 mV ⁽⁷⁾⁽⁸⁾		90	145		mA
			−40°C ≤ T _J ≤ 125°C	75			
		Sinking to ground ΔV _{IN} = −200 mV ⁽⁷⁾⁽⁸⁾		90	145		
			−40°C ≤ T _J ≤ 125°C	75			
I _{OUT}	Output current	Sourcing, V _O = +0.8 V Sinking, V _O = −0.8 V		100			mA
POWER SUPPLY							
PSRR	Power supply rejection ratio	V _S = ±2 V to ±3 V		82	90		dB
			−40°C ≤ T _J ≤ 125°C	80			
I _S	Supply current (per channel)	No load		11.4		16	mA
			−40°C ≤ T _J ≤ 125°C	18			

(7) Applies to both single-supply and split-supply operation. Continuous short circuit operation at elevated ambient temperature can result in exceeding the maximum allowed junction temperature of 150°C .

(8) Short circuit test is a momentary test. Output short circuit duration is 1.5 ms.

6.6 Electrical Characteristics ± 6 V

Unless otherwise specified, all limits ensured at $T_A = 25^\circ\text{C}$, $V^+ = 6$ V, $V^- = -6$ V, $V_{CM} = 0$ V, $A_V = +20$, $R_F = 500\ \Omega$, $R_L = 100\ \Omega$. See ⁽¹⁾.

PARAMETER		TEST CONDITIONS	MIN ⁽²⁾	TYP ⁽³⁾	MAX ⁽²⁾	UNIT
DYNAMIC PERFORMANCE						
f_{CL}	–3-dB BW	$V_O = 400$ mV _{PP}		95		MHz
SR	Slew rate ⁽⁴⁾	$V_O = 2$ V _{PP} , $A_V = +20$		350		V/ μ s
		$V_O = 2$ V _{PP} , $A_V = +10$		400		
t_r	Rise time	$V_O = 400$ mV Step, 10% to 90%		3.7		ns
t_f	Fall time	$V_O = 400$ mV Step, 10% to 90%		3.7		ns
t_s	Settling time 0.1%	$V_O = 2$ V _{PP} (Step)		18		ns
DISTORTION and NOISE RESPONSE						
e_n	Input referred voltage noise	$f = 1$ MHz		0.92		nV/ $\sqrt{\text{Hz}}$
i_n	Input referred current noise	$f = 1$ MHz		2.3		pA/ $\sqrt{\text{Hz}}$
HD2	2 nd harmonic distortion	$f_C = 10$ MHz, $V_O = 1$ V _{PP} , $R_L = 100\ \Omega$		–63		dBc
HD3	3 rd harmonic distortion	$f_C = 10$ MHz, $V_O = 1$ V _{PP} , $R_L = 100\ \Omega$		–80		dBc
INPUT CHARACTERISTICS						
V_{OS}	Input offset voltage	$V_{CM} = 0$ V		–0.5	± 0.10	± 0.5 mV
			$-40^\circ\text{C} \leq T_J \leq 125^\circ\text{C}$	–0.7	± 0.7	
	Average drift ⁽⁵⁾	$V_{CM} = 0$ V			± 0.2	$\mu\text{V}/^\circ\text{C}$
I_{OS}	Input offset current	$V_{CM} = 0$ V		–1.1	0.05	1.1 μ A
			$-40^\circ\text{C} \leq T_J \leq 125^\circ\text{C}$	–2.5		2.5
	Average drift ⁽⁵⁾	$V_{CM} = 0$ V			0.7	nA/ $^\circ\text{C}$
I_B	Input bias current	$V_{CM} = 0$ V			13	± 20 μ A
			$-40^\circ\text{C} \leq T_J \leq 125^\circ\text{C}$			± 25
	Average drift ⁽⁵⁾	$V_{CM} = 0$ V			12	nA/ $^\circ\text{C}$
R_{IN}	Input resistance ⁽⁶⁾	Common Mode		6.6		M Ω
		Differential Mode		4.6		k Ω
C_{IN}	Input capacitance ⁽⁶⁾	Common Mode		0.9		pF
		Differential Mode		2.0		
CMRR	Common-mode rejection ratio	Input referred, $V_{CM} = -4.5$ V to $+5.25$ V		90	95	dB
		Input referred, $V_{CM} = -4.5$ V to $+5$ V	$-40^\circ\text{C} \leq T_J \leq 125^\circ\text{C}$	87		

- (1) Electrical table values apply only for factory testing conditions at the temperature indicated. Factory testing conditions result in very limited self-heating of the device such that $T_J = T_A$. No ensured specification of parametric performance is indicated in the electrical tables under conditions of internal self-heating where $T_J > T_A$. Absolute maximum ratings indicate junction temperature limits beyond which the device may be permanently degraded, either mechanically or electrically.
- (2) All limits are specified by testing or statistical analysis.
- (3) Typical Values represent the most likely parametric norm.
- (4) Slew rate is the slowest of the rising and falling slew rates.
- (5) Average drift is determined by dividing the change in parameter at temperature extremes into the total temperature change.
- (6) Simulation results.

Electrical Characteristics ± 6 V (continued)

Unless otherwise specified, all limits ensured at $T_A = 25^\circ\text{C}$, $V^+ = 6$ V, $V^- = -6$ V, $V_{CM} = 0$ V, $A_V = +20$, $R_F = 500\ \Omega$, $R_L = 100\ \Omega$. See ⁽¹⁾.

PARAMETER		TEST CONDITIONS	MIN ⁽²⁾	TYP ⁽³⁾	MAX ⁽²⁾	UNIT
TRANSFER CHARACTERISTICS						
A _{VOL}	Large signal voltage gain	R _L = 100 Ω, V _O = −3 V to +3 V		77	81	dB
			−40°C ≤ T _J ≤ 125°C	72		
OUTPUT CHARACTERISTICS						
V _O	Output swing	R _L = 100 Ω		±4.4	±4.9	V
			−40°C ≤ T _J ≤ 125°C	±4.3		
		No load		±4.8	±5.2	
			−40°C ≤ T _J ≤ 125°C	±4.65		
R _O	Output impedance	f ≤ 100 KHz		10		mΩ
I _{SC}	Output short circuit current	Sourcing to ground ΔV _{IN} = 200 mV ⁽⁷⁾⁽⁸⁾		100	156	mA
			−40°C ≤ T _J ≤ 125°C	85		
		Sinking to ground ΔV _{IN} = −200 mV ⁽⁷⁾⁽⁸⁾		100	156	
			−40°C ≤ T _J ≤ 125°C	85		
I _{OUT}	Output current	Sourcing, V _O = +4.3 V Sinking, V _O = −4.3 V		100		mA
POWER SUPPLY						
PSRR	Power supply rejection ratio	V _S = ±5.4 V to ±6.6 V		82	88	dB
			−40°C ≤ T _J ≤ 125°C	80		
I _S	Supply current (per channel)	No load		12	16	mA
			−40°C ≤ T _J ≤ 125°C		18	

(7) Applies to both single-supply and split-supply operation. Continuous short circuit operation at elevated ambient temperature can result in exceeding the maximum allowed junction temperature of 150°C .

(8) Short circuit test is a momentary test. Output short circuit duration is 1.5 ms.

6.7 Typical Characteristics

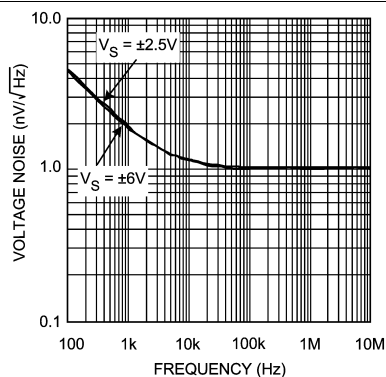


Figure 1. Voltage Noise vs Frequency

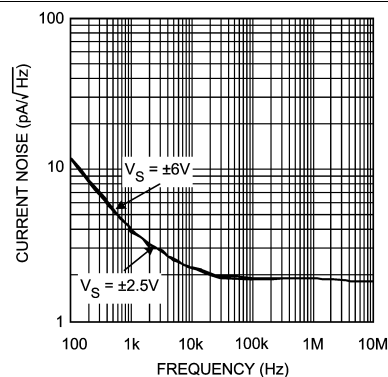
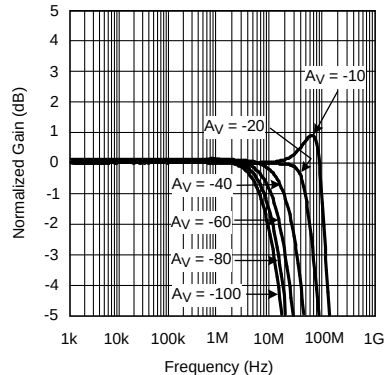
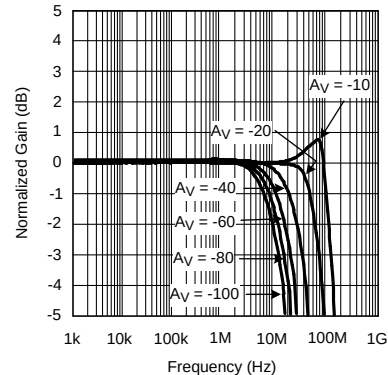


Figure 2. Current Noise vs Frequency



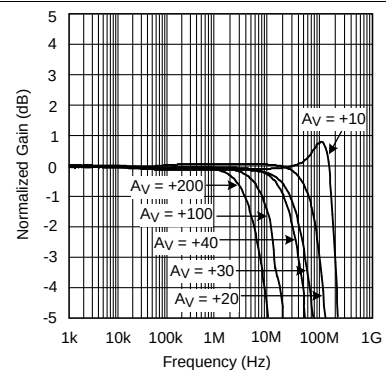
$V_S = \pm 2.5\text{ V}$
 $V_{IN} = 5\text{ mVpp}$
 $R_L = 100\ \Omega$

Figure 3. Inverting Frequency Response



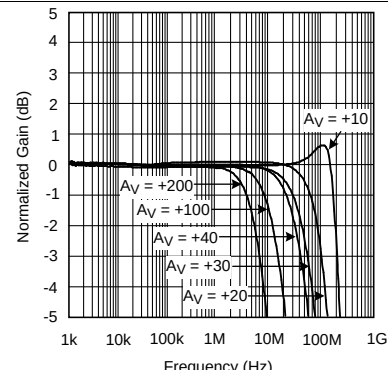
$V_S = \pm 6\text{ V}$
 $V_{IN} = 5\text{ mVpp}$
 $R_L = 100\ \Omega$

Figure 4. Inverting Frequency Response



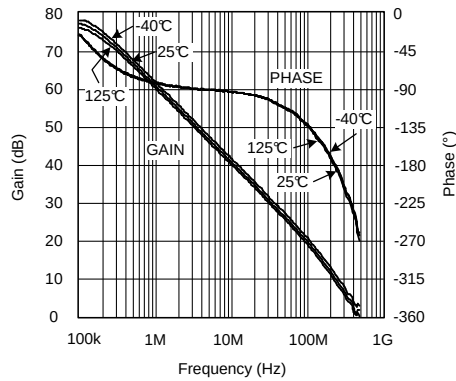
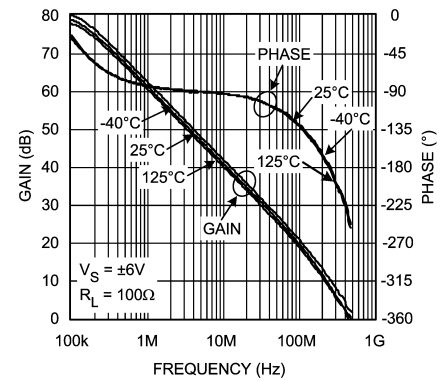
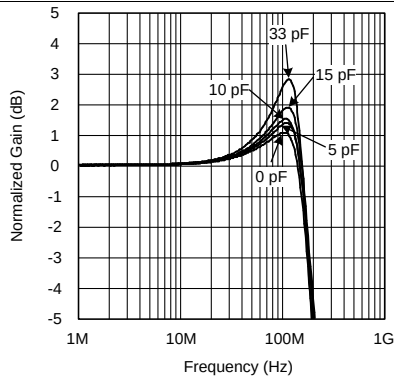
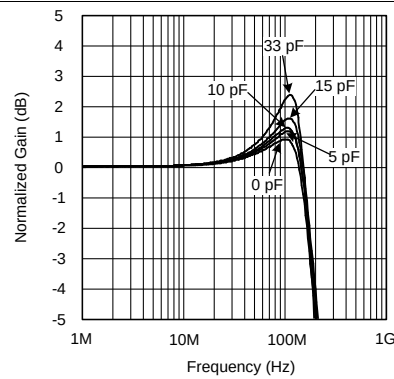
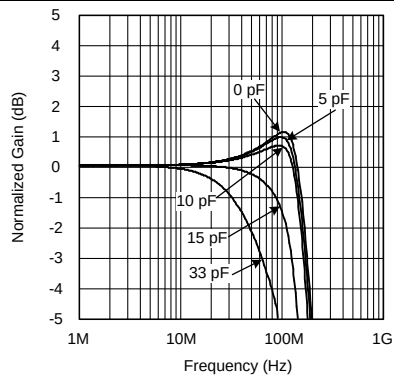
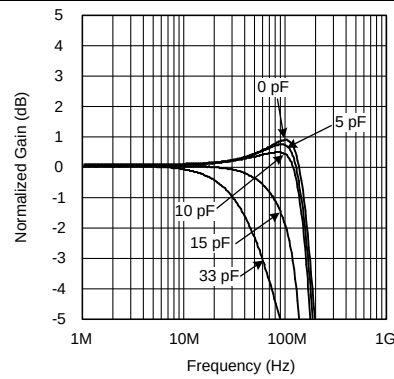
$V_S = \pm 2.5\text{ V}$
 $R_F = 500\ \Omega$
 $V_O = 2\text{ Vpp}$

Figure 5. Non-Inverting Frequency Response

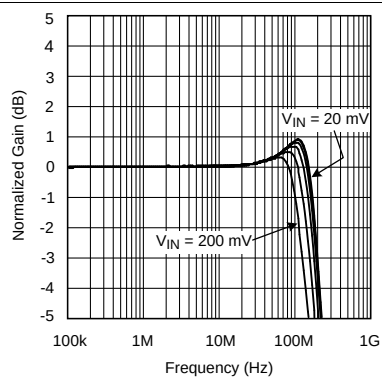


$V_S = \pm 6\text{ V}$
 $R_F = 500\ \Omega$
 $V_O = 2\text{ Vpp}$

Figure 6. Non-Inverting Frequency Response

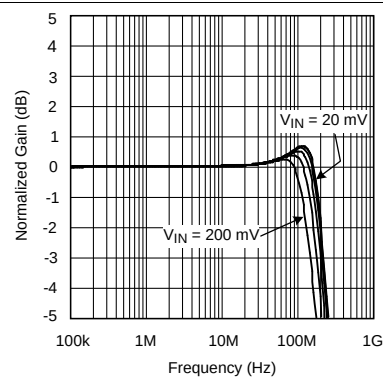
Typical Characteristics (continued)

Figure 7. Open Loop Frequency Response Over Temperature

Figure 8. Open Loop Frequency Response Over Temperature

Figure 9. Frequency Response with Cap. Loading

Figure 10. Frequency Response with Cap. Loading

Figure 11. Frequency Response with Cap. Loading

Figure 12. Frequency Response with Cap. Loading

Typical Characteristics (continued)



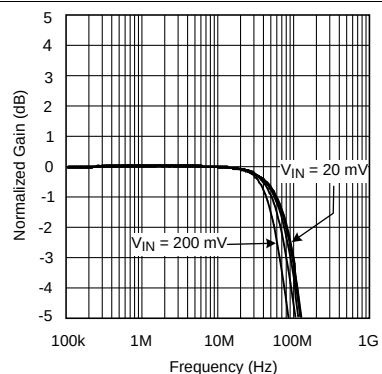
$V_S = \pm 2.5 \text{ V}$
 $A_V = +10$
 $R_F = 500 \, \Omega$

Figure 13. Non-Inverting Frequency Response Varying V_{IN}



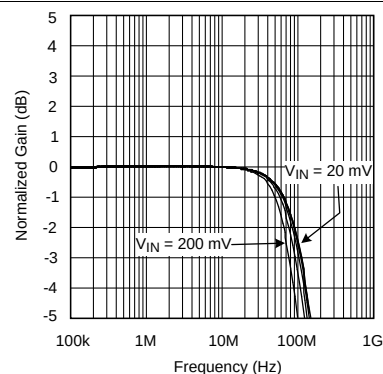
$V_S = \pm 6 \text{ V}$
 $A_V = +10$
 $R_F = 500 \, \Omega$

Figure 14. Non-Inverting Frequency Response Varying V_{IN}



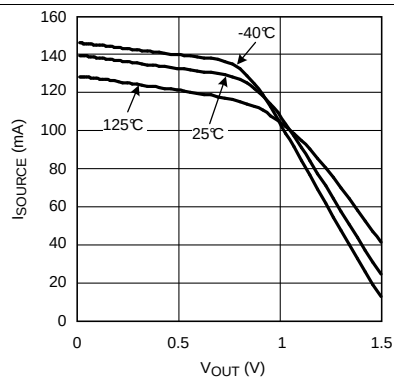
$V_S = \pm 2.5 \text{ V}$
 $A_V = +20$
 $R_F = 500 \, \Omega$

Figure 15. Non-Inverting Frequency Response Varying V_{IN}



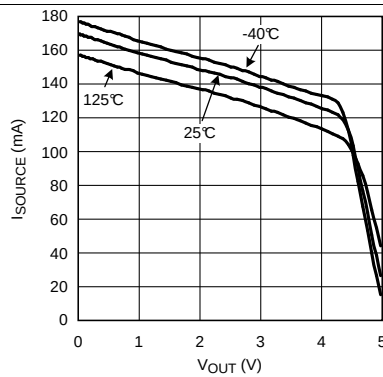
$V_S = \pm 6 \text{ V}$
 $A_V = +20$
 $R_F = 500 \, \Omega$

Figure 16. Non-Inverting Frequency Response Varying V_{IN}



$V_S = \pm 2.5 \text{ V}$

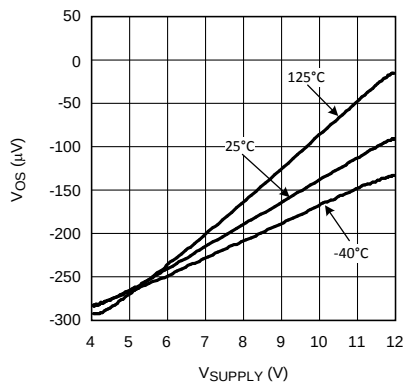
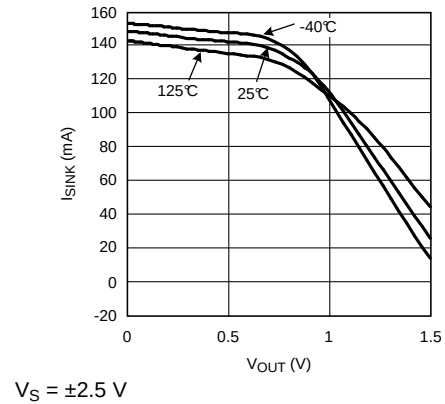
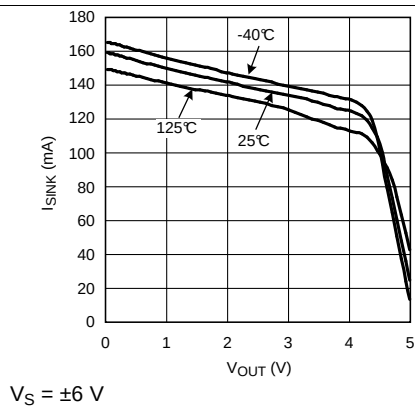
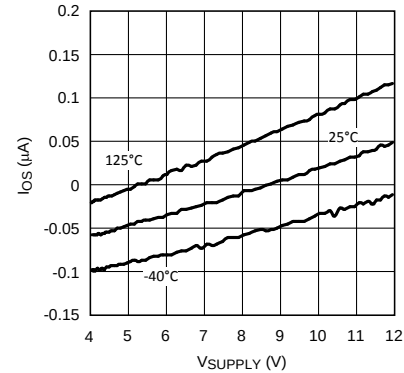
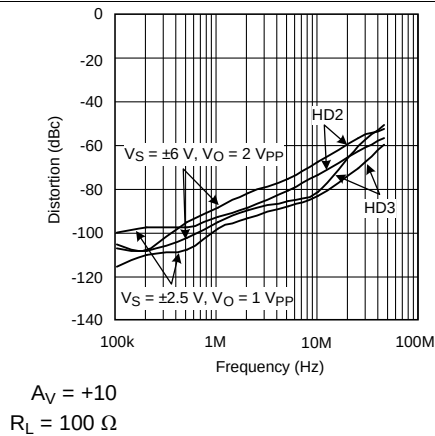
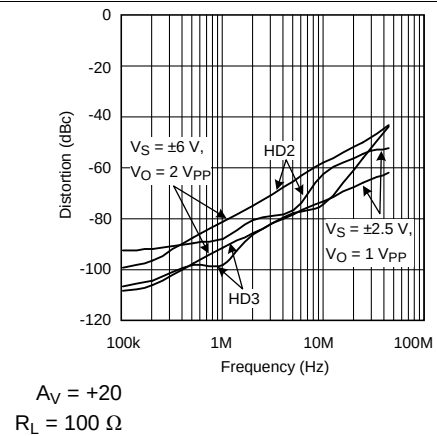
Figure 17. Sourcing Current vs V_{OUT}



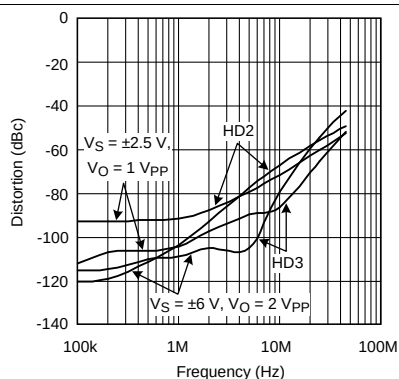
$V_S = \pm 6 \text{ V}$

Figure 18. Sourcing Current vs V_{OUT}

Typical Characteristics (continued)

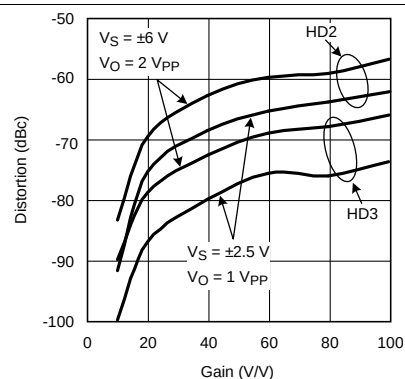

Figure 19. V_{OS} vs V_{SUPPLY}

Figure 20. Sinking Current vs V_{OUT}

Figure 21. Sinking Current vs V_{OUT}

Figure 22. I_{OS} vs V_{SUPPLY}

Figure 23. Distortion vs Frequency

Figure 24. Distortion vs Frequency

Typical Characteristics (continued)



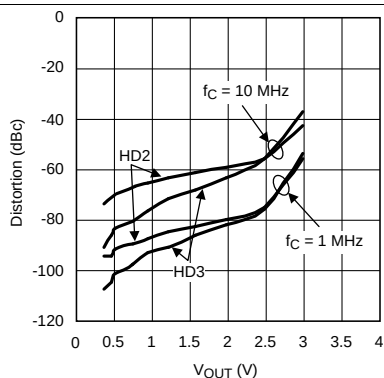
$A_V = +20$
 $R_L = 500 \Omega$

Figure 25. Distortion vs Frequency



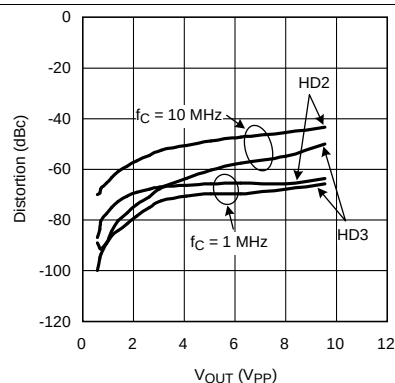
$V_S = \pm 6 V$
 $V_O = 2 V_{pp}$

Figure 26. Distortion vs Gain



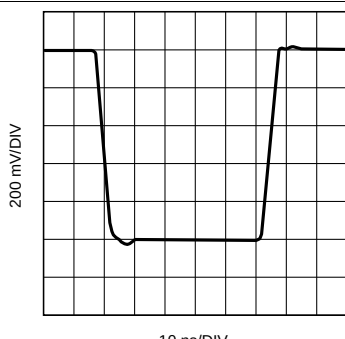
$A_V = +20$
 $A_V = \pm 2.5 V$
 $R_L = 100 \Omega$

Figure 27. Distortion vs V_{OUT} Peak to Peak



$A_V = +20$
 $V_S = \pm 6 V$
 $R_L = 100 \Omega$

Figure 28. Distortion vs V_{OUT} Peak to Peak



$V_S = \pm 2.5 V$
 $V_O = 1 V_{pp}$
 $A_V = +10$
 $R_L = 100 \Omega$

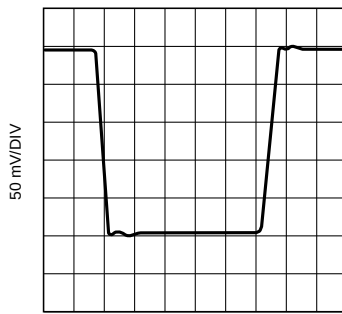
Figure 29. Non-Inverting Large Signal Pulse Response



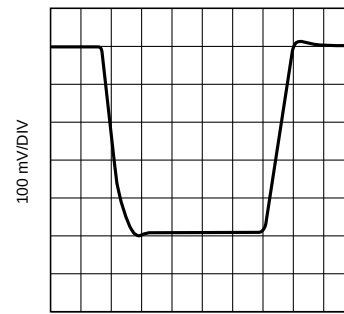
$V_S = \pm 6 V$
 $V_O = 1 V_{pp}$
 $A_V = +20$
 $R_L = 100 \Omega$

Figure 30. Non-Inverting Large Signal Pulse Response

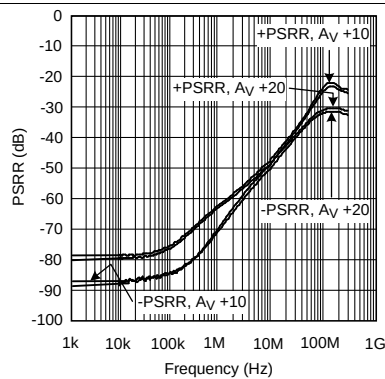
Typical Characteristics (continued)



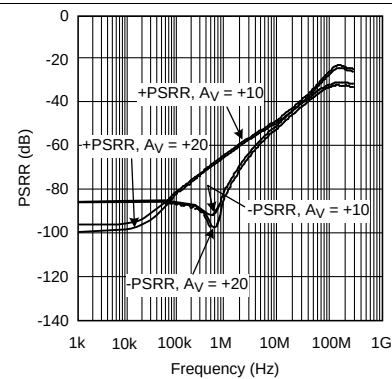
$V_S = \pm 2.5 \text{ V}$
 $V_O = 200 \text{ mV}$
 $A_V = +10$
 $R_L = 100 \Omega$

Figure 31. Non-Inverting Small Signal Pulse Response


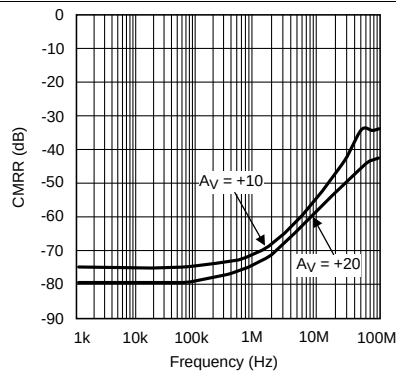
$V_S = \pm 6 \text{ V}$
 $V_O = 500 \text{ mV}$
 $A_V = +20$
 $R_L = 100 \Omega$

Figure 32. Non-Inverting Small Signal Pulse Response


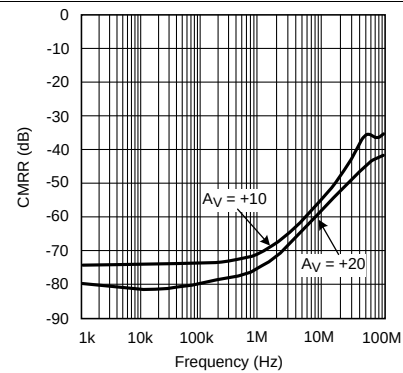
$V_S = \pm 2.5 \text{ V}$

Figure 33. PSRR vs Frequency


$V_S = \pm 6 \text{ V}$

Figure 34. PSRR vs Frequency


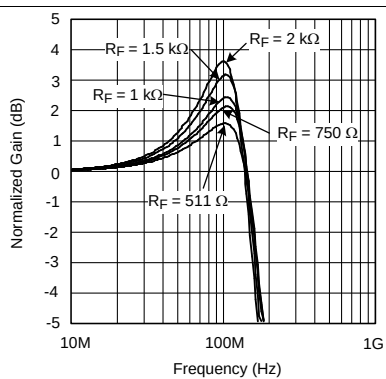
$V_S = \pm 2.5 \text{ V}$
 $V_{IN} = 5 \text{ mVpp}$

Figure 35. Input Referred CMRR vs Frequency


$V_S = \pm 6 \text{ V}$
 $V_{IN} = 5 \text{ mVpp}$

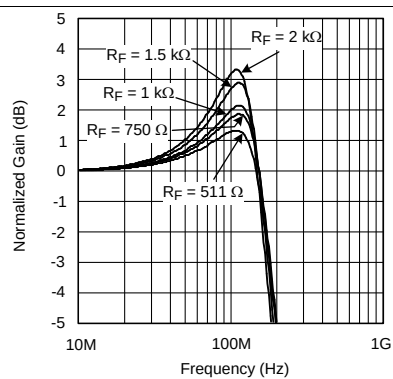
Figure 36. Input Referred CMRR vs Frequency

Typical Characteristics (continued)



$V_S = \pm 2.5 \text{ V}$
 $A_V = +10$
 $R_L = 100 \text{ } \Omega$

Figure 37. Amplifier Peaking with Varying R_F



$V_S = \pm 6 \text{ V}$
 $A_V = +10$
 $R_L = 100 \text{ } \Omega$

Figure 38. Amplifier Peaking with Varying R_F

7 Detailed Description

7.1 Overview

The LMH6624-MIL device is a very-wide-gain bandwidth, ultra-low-noise voltage feedback operational amplifier. The excellent performance of the device enables applications such as medical diagnostic ultrasound, magnetic tape and disk storage and fiber-optics to achieve maximum high-frequency signal-to-noise ratios. The set of characteristic plots in [Typical Characteristics](#) illustrates many of the performance trade-offs. The following discussion will demonstrate the proper selection of external components to achieve optimum system performance.

7.2 Feature Description

7.2.1 Bias Current Cancellation

To cancel the bias current errors of the non-inverting configuration, the parallel combination of the gain setting (R_g) and feedback (R_f) resistors should equal the equivalent source resistance (R_{seq}) as defined in [Figure 39](#). Combining this constraint with the non-inverting gain equation also seen in [Figure 39](#), allows both R_f and R_g to be determined explicitly from the following equations:

$$R_f = A_V R_{seq} \quad (1)$$

$$R_g = R_f / (A_V - 1) \quad (2)$$

When driven from a 0- Ω source, such as the output of an op amp, the non-inverting input of the LMH6624-MIL should be isolated with at least a 25- Ω series resistor.

As seen in [Figure 40](#), bias current cancellation is accomplished for the inverting configuration by placing a resistor (R_b) on the non-inverting input equal in value to the resistance seen by the inverting input ($R_f || (R_g + R_s)$). R_b should be no less than 25 Ω for optimum LMH6624-MIL performance. A shunt capacitor can minimize the additional noise of R_b .

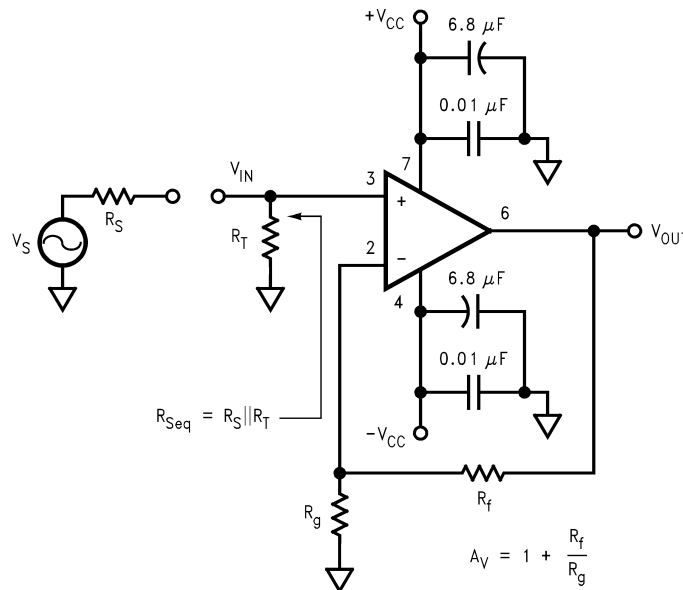


Figure 39. Non-Inverting Amplifier Configuration

Feature Description (continued)

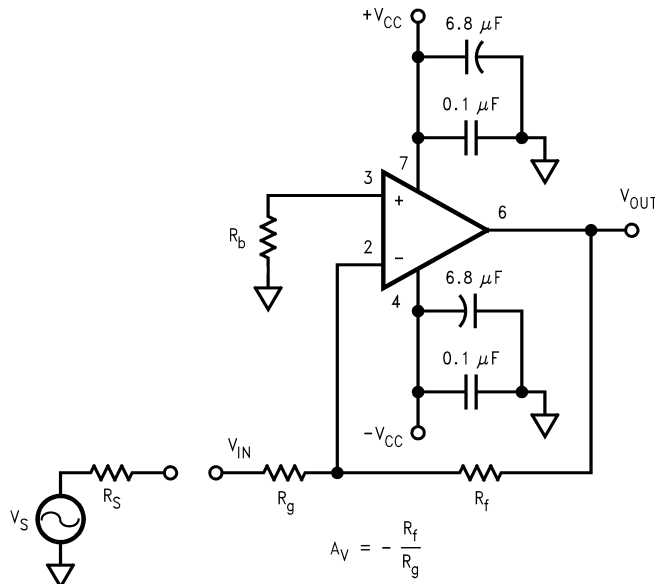


Figure 40. Inverting Amplifier Configuration

7.2.2 Total Input Noise vs Source Resistance

To determine maximum signal-to-noise ratios from the LMH6624-MIL, an understanding of the interaction between the intrinsic noise sources and the noise arising from external resistors is necessary.

Figure 41 describes the noise model for the non-inverting amplifier configuration showing all noise sources. In addition to the intrinsic input voltage noise (e_n) and current noise ($i_n = i_n^+ = i_n^-$) source, there is also thermal voltage noise ($e_t = \sqrt{4KTR}$) associated with each of the external resistors. Equation 3 provides the general form for total equivalent input voltage noise density (e_{ni}). Equation 4 is a simplification of Equation 3 that assumes $R_f || R_g = R_{seq}$ for bias current cancellation. Figure 42 illustrates the equivalent noise model using this assumption. Figure 43 is a plot of e_{ni} against equivalent source resistance (R_{seq}) with all of the contributing voltage noise sources of Equation 4. This plot gives the expected e_{ni} for a given (R_{seq}) which assumes $R_f || R_g = R_{seq}$ for bias current cancellation. The total equivalent output voltage noise (e_{no}) is $e_{ni} \cdot A_V$.

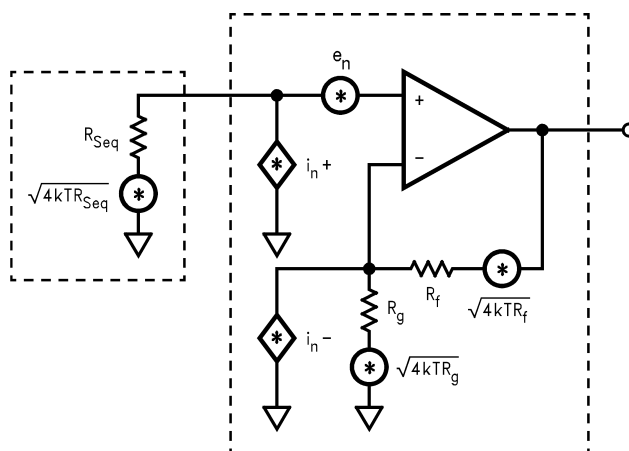


Figure 41. Non-Inverting Amplifier Noise Model

$$e_{ni} = \sqrt{e_n^2 + (i_{n+} R_{Seq})^2 + 4kTR_{Seq} + (i_{n-} (R_f || R_g))^2 + 4kT(R_f || R_g)} \quad (3)$$

Feature Description (continued)

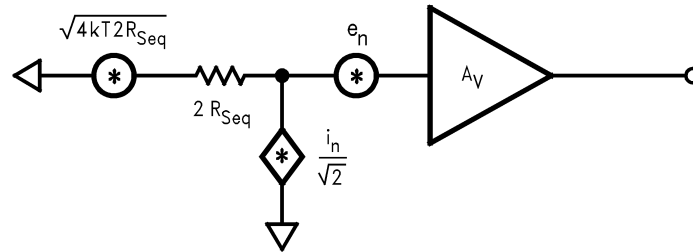


Figure 42. Noise Model with $R_f \parallel R_g = R_{seq}$

$$e_{ni} = \sqrt{e_n^2 + 2(i_n R_{seq})^2 + 4kT(2R_{seq})} \quad (4)$$

As seen in [Figure 43](#), e_{ni} is dominated by the intrinsic voltage noise (e_n) of the amplifier for equivalent source resistances below 26 Ω . Between 26 Ω and 3.1 k Ω , e_{ni} is dominated by the thermal noise ($e_t = \sqrt{4kT(2R_{seq})}$) of the equivalent source resistance R_{seq} . Above 3.1 k Ω , e_{ni} is dominated by the amplifier's current noise ($i_n = \sqrt{2} i_n R_{seq}$). When $R_{seq} = 283 \Omega$ (that is, $R_{seq} = e_n / \sqrt{2} i_n$) the contribution from voltage noise and current noise of LMH6624-MIL is equal. For example, configured with a gain of +20V/V giving a –3 dB of 90 MHz and driven from $R_{seq} = R_f \parallel R_g = 25 \Omega$ ($e_{ni} = 1.3 \text{ nV}/\sqrt{\text{Hz}}$ from [Figure 43](#)), the LMH6624-MIL produces a total output noise voltage ($e_{ni} \times 20 \text{ V/V} \times \sqrt{(1.57 \times 90 \text{ MHz})}$) of 309 μV_{rms} .

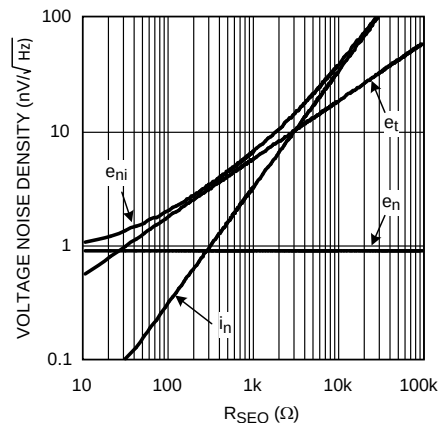


Figure 43. Voltage Noise Density vs Source Resistance

If bias current cancellation is not a requirement, then $R_f \parallel R_g$ need not equal R_{seq} . In this case, according to [Equation 3](#), $R_f \parallel R_g$ should be as low as possible to minimize noise. Results similar to [Equation 3](#) are obtained for the inverting configuration of [Figure 40](#) if R_{seq} is replaced by R_b and R_g is replaced by $R_g + R_s$. With these substitutions, [Equation 3](#) will yield an e_{ni} referred to the non-inverting input. Referring e_{ni} to the inverting input is easily accomplished by multiplying e_{ni} by the ratio of non-inverting to inverting gains.

Feature Description (continued)

7.2.3 Noise Figure

Noise Figure (NF) is a measure of the noise degradation caused by an amplifier.

$$NF = 10\text{LOG} \left\{ \frac{S_i / N_i}{S_o / N_o} \right\} = 10\text{LOG} \left\{ \frac{e_{ni}^2}{e_t^2} \right\} \quad (5)$$

The Noise Figure formula is shown in Equation 5. The addition of a terminating resistor R_T , reduces the external thermal noise but increases the resulting NF. The NF is increased because R_T reduces the input signal amplitude thus reducing the input SNR.

$$NF = 10 \text{ LOG} \left[\frac{e_n^2 + i_n^2 (R_{Seq}^2 + (R_f || R_g)^2) + 4KT (R_{Seq} + (R_f || R_g))}{4KT (R_{Seq} + (R_f || R_g))} \right] \quad (6)$$

The noise figure is related to the equivalent source resistance (R_{seq}) and the parallel combination of R_f and R_g . To minimize "Noise Figure":

- Minimize $R_f || R_g$
- Choose the Optimum R_S (R_{OPT})

R_{OPT} is the point at which the NF curve reaches a minimum and is approximated by:

$$R_{OPT} \approx \frac{e_n}{i_n} \quad (7)$$

7.2.4 Low-Noise Integrator

The LMH6624-MIL device implements a deBoo integrator shown in Figure 44. Positive feedback maintains integration linearity. The low-input-offset voltage of the LMH6624-MIL device and matched input allow bias current cancellation and provide for very precise integration. Keeping R_G and R_S low helps maintain dynamic stability.

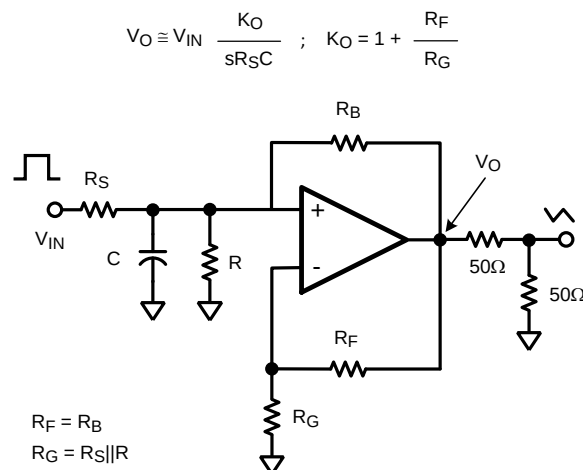


Figure 44. Low-Noise Integrator

Feature Description (continued)

7.2.5 High-Gain Sallen-Key Active Filters

The LMH6624-MIL device is well suited for high-gain Sallen-Key type of active filters. Figure 45 shows the 2nd order Sallen-Key low-pass-filter topology. Using component predistortion methods discussed in Application Note OA-21, *Component Pre-Distortion for Sallen Key Filters* (SNOA369) will enable the proper selection of components for these high-frequency filters.

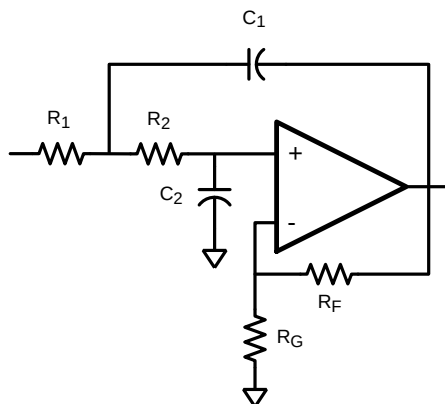
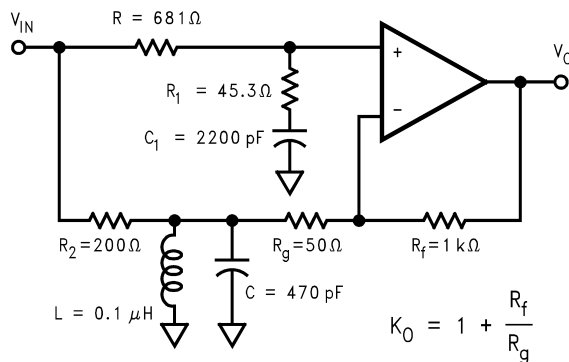


Figure 45. Sallen-Key Active Filter Topology

7.2.6 Low-Noise Magnetic Media Equalizer

The LMH6624-MIL device implements a high-performance, low-noise equalizer for such applications as magnetic tape channels as shown in Figure 46. The circuit combines an integrator with a bandpass filter to produce the low-noise equalization. The simulated frequency response is illustrated in Figure 47.



$$\frac{V_O}{V_{IN}} = K_0 \left(\frac{sC_1 R_1 + 1}{sC_1 (R_1 + R) + 1} - \left(\frac{R_f}{R_f + R_g} \right) \frac{sLR_g}{s^2 LCR_2 R_g + sL(R_2 + R_g) + R_2 R_g} \right)$$

Figure 46. Low-Noise Magnetic Media Equalizer

Feature Description (continued)

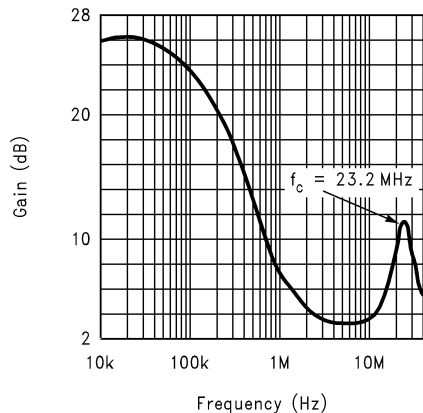


Figure 47. Equalizer Frequency Response

7.3 Device Functional Modes

7.3.1 Single Supply Operation

The LMH6624-MIL device can be operated with single power supply as shown in Figure 48. Both the input and output are capacitively coupled to set the DC operating point.

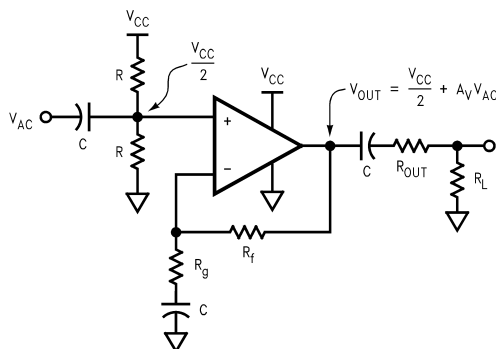


Figure 48. Single Supply Operation

8 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

A transimpedance amplifier is used to convert the small output current of a photodiode to a voltage, while maintaining a near constant voltage across the photodiode to minimize non-linearity. Extracting the small signal requires high gain and a low-noise amplifier, and therefore, the LMH6624-MIL device is ideal for such an application in order to maximize SNR. Furthermore, because of the large gain (R_F value) needed, the device used must be high speed so that even with high-noise gain (due to the interaction of the feedback resistor and photodiode capacitance), bandwidth is not heavily impacted.

Figure 39 implements a high-speed, single supply, low-noise transimpedance amplifier commonly used with photo-diodes. The transimpedance gain is set by R_F .

8.2 Typical Application

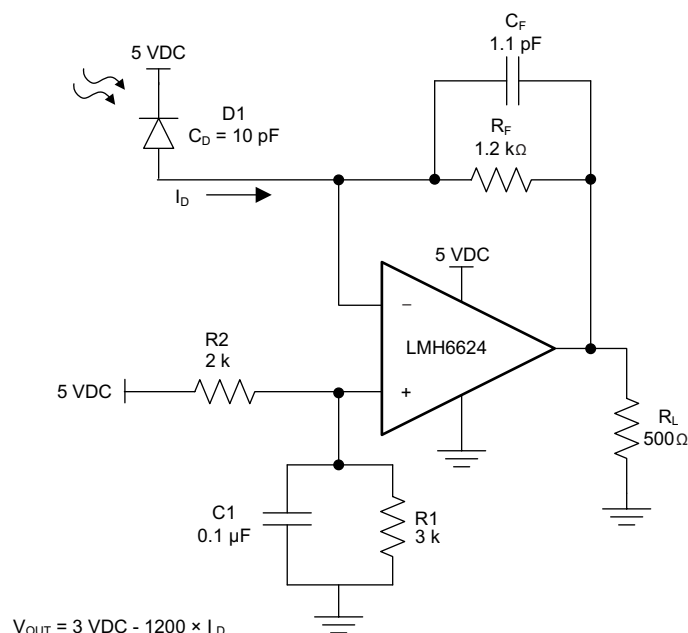


Figure 49. Application Schematic

Typical Application (continued)

8.2.1 Design Requirements

Figure 50 shows the Noise Gain (NG) and transfer function (I-V Gain). As with most transimpedance amplifiers, it is required to compensate for the additional phase lag (noise gain zero at f_z) created by the total input capacitance: C_D (diode capacitance) + C_{CM} (CM input capacitance) + C_{DIFF} (DIFF input capacitance) looking into R_F . This is accomplished by placing C_F across R_F to create enough phase lead (Noise Gain pole at f_p) to stabilize the loop.

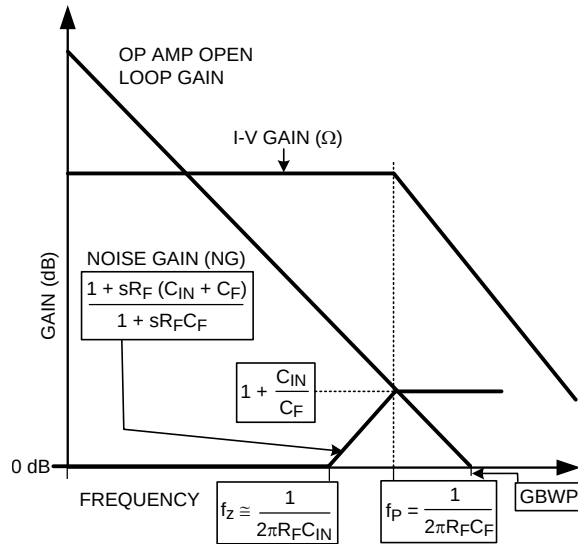


Figure 50. Transimpedance Amplifier Noise Gain and Transfer Function

8.2.2 Detailed Design Procedure

The optimum value of C_F is given by Equation 8 resulting in the I-V –3dB bandwidth shown in Equation 9, or around 124 MHz in this case, assuming GBWP = 1.5 GHz, C_{CM} (CM input capacitance) = 0.9 pF, and C_{DIFF} (DIFF input capacitance) = 2 pF. This C_F value is a “starting point” and C_F needs to be tuned for the particular application as it is often less than 1 pF and thus is easily affected by board parasitics.

Optimum C_F Value:

$$C_F = \sqrt{\frac{C_{IN}}{2\pi(GBWP)R_F}} \quad (8)$$

Resulting –3dB Bandwidth:

$$f_{-3dB} \cong \sqrt{\frac{GBWP}{2\pi R_F C_{IN}}} \quad (9)$$

Equation 10 provides the total input current noise density (i_{ni}) equation for the basic transimpedance configuration and is plotted against feedback resistance (R_F) showing all contributing noise sources in Figure 51. The plot indicates the expected total equivalent input current noise density (i_{ni}) for a given feedback resistance (R_F). This is depicted in the schematic of Figure 52 where total equivalent current noise density (i_{ni}) is shown at the input of a noiseless amplifier and noiseless feedback resistor (R_F). The total equivalent output voltage noise density (e_{no}) is $i_{ni} \cdot R_F$. Noise Equation for Transimpedance Amplifier:

$$i_{ni} = \sqrt{i_n^2 + \left(\frac{e_n}{R_f}\right)^2 + \frac{4kT}{R_f}} \quad (10)$$

Typical Application (continued)

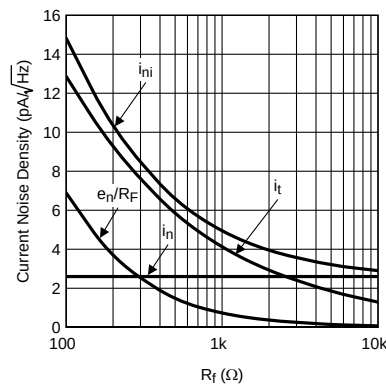


Figure 51. Current Noise Density vs Feedback Resistance

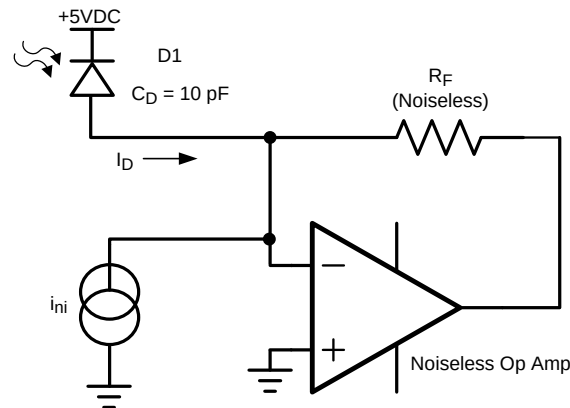


Figure 52. Transimpedance Amplifier Equivalent Input Source Mode

From Figure 53, it is clear that with the LMH6624-MIL extremely low-noise characteristics, for $R_F < 3 \text{ k}\Omega$, the noise performance is entirely dominated by R_F thermal noise. Only above this R_F threshold, the input noise current (i_n) of LMH6624-MIL becomes a factor and at no R_F setting does the LMH6624-MIL input noise voltage play a significant role. This noise analysis has ignored the possible noise gain increase, due to photo-diode capacitance, at higher frequencies.

8.2.3 Application Curve

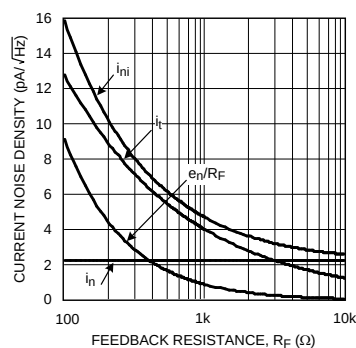


Figure 53. Current Noise Density vs Feedback Resistance

9 Power Supply Recommendations

The LMH6624-MIL device can operate off a single supply or with dual supplies as long as the input CM voltage range (CMIR) has the required headroom to either supply rail. Supplies should be decoupled with low-inductance, often ceramic, capacitors to ground less than 0.5 in from the device pins. The use of ground plane is recommended, and as in most high-speed devices, it is advisable to remove ground plane close to device sensitive pins such as the inputs.

10 Layout

10.1 Layout Guidelines

TI suggests the copper patterns on the evaluation boards shown in [Figure 54](#) and [Figure 55](#) as a guide for high-frequency layout. These boards are also useful as an aid in device testing and characterization. As is the case with all high-speed amplifiers, accepted-practice RF design technique on the PCB layout is mandatory. Generally, a good high-frequency layout exhibits a separation of power supply and ground traces from the inverting input and output pins as shown in [Figure 54](#). Parasitic capacitances between these nodes and ground may cause frequency response peaking and possible circuit oscillations. See Application Note OA-15, *Frequent Faux Pas in Applying Wideband Current Feedback Amplifiers* ([SNOA367](#)) for more information. Use high-quality chip capacitors with values in the range of 1000 pF to 0.1 μ F for power supply bypassing as shown in [Figure 54](#). One terminal of each chip capacitor is connected to the ground plane and the other terminal is connected to a point that is as close as possible to each supply pin as allowed by the manufacturer's design rules. In addition, connect a tantalum capacitor with a value between 4.7 μ F and 10 μ F in parallel with the chip capacitor. Signal lines connecting the feedback and gain resistors should be as short as possible to minimize inductance and microstrip line effect as shown in [Figure 55](#). Place input and output termination resistors as close as possible to the input/output pins. Traces greater than 1 inch in length should be impedance matched to the corresponding load termination.

Symmetry between the positive and negative paths in the layout of differential circuitry should be maintained to minimize the imbalance of amplitude and phase of the differential signal.

Component value selection is another important parameter in working with high-speed and high-performance amplifiers. Choosing external resistors that are large in value compared to the value of other critical components will affect the closed loop behavior of the stage because of the interaction of these resistors with parasitic capacitances. These parasitic capacitors could either be inherent to the device or be a by-product of the board layout and component placement. Moreover, a large resistor will also add more thermal noise to the signal path. Either way, keeping the resistor values low will diminish this interaction. On the other hand, choosing very-low-value resistors could load down nodes and will contribute to higher overall power dissipation and high distortion.

DEVICE	PACKAGE	EVALUATION BOARD PART NUMBER
LMH6624MF	SOT-23-5	LMH730216
LMH6624MA	SOIC-8	LMH730227

10.2 Layout Example

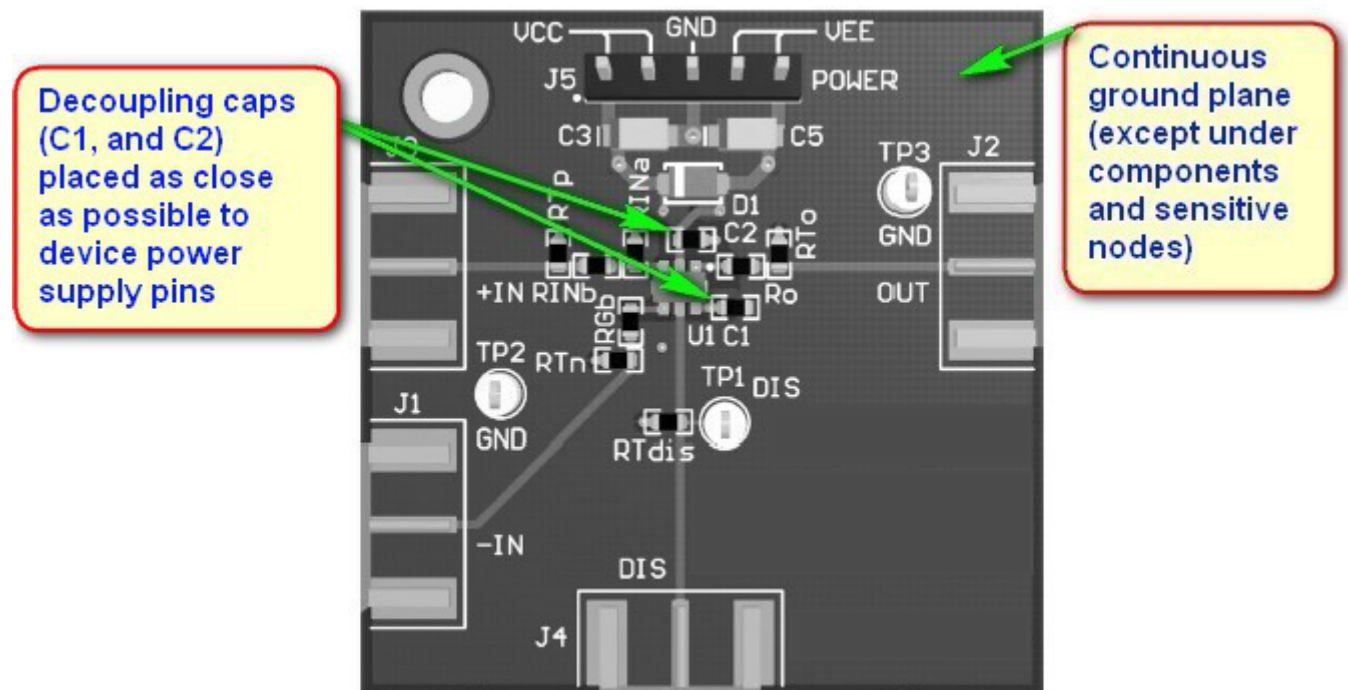


Figure 54. EVM Board Layout Example (Top)

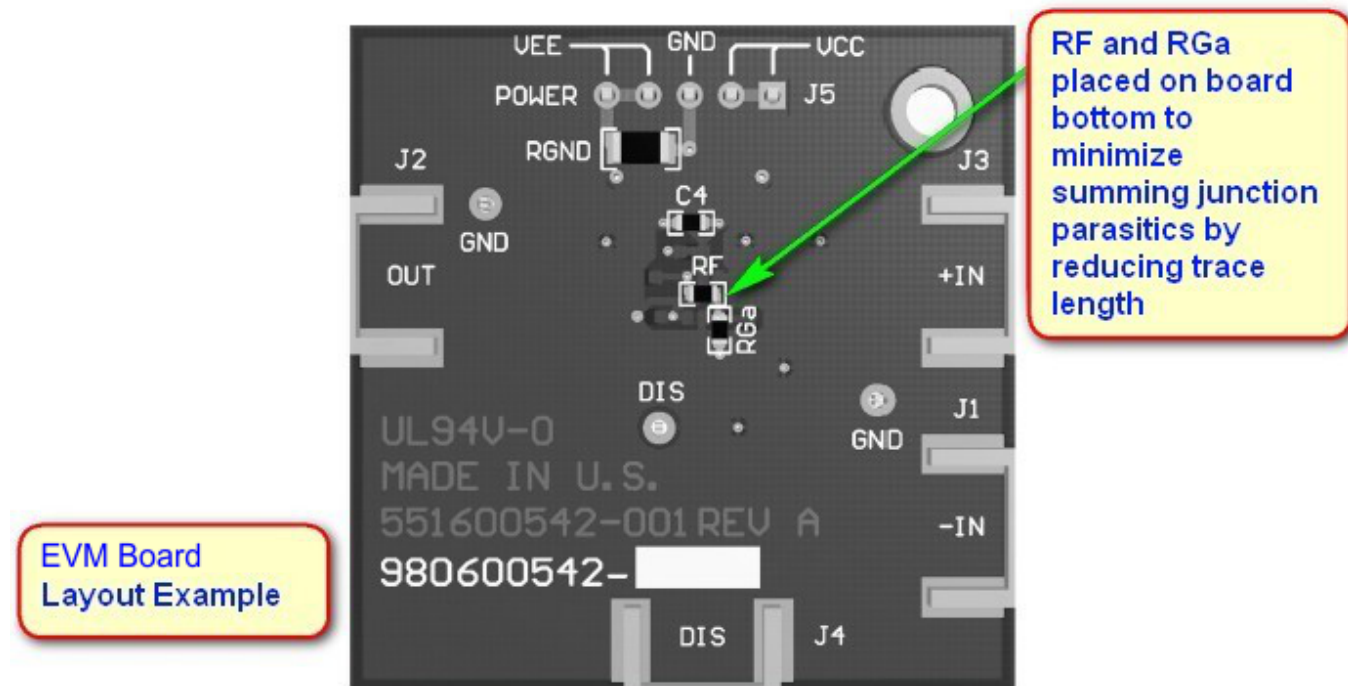


Figure 55. EVM Board Layout Example (Bottom)

11 Device and Documentation Support

11.1 Documentation Support

11.1.1 Related Documentation

- *Absolute Maximum Ratings for Soldering* ([SNOA549](#))
- *Frequent Faux Pas in Applying Wideband Current Feedback Amplifiers*, Application Note OA-15 ([SNOA367](#))
- *Semiconductor and IC Package Thermal Metrics* ([SPRA953](#))

11.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

11.3 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

11.4 Trademarks

E2E is a trademark of Texas Instruments.
All other trademarks are the property of their respective owners.

11.5 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

11.6 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
LMH6624 MDC	Active	Production	DIESALE (Y) 0	400 NOT REQUIRED	Yes	Call TI	Level-1-NA-UNLIM	-40 to 85	
LMH6624-MDC.A	Active	Production	DIESALE (Y) 0	400 NOT REQUIRED	Yes	Call TI	Level-1-NA-UNLIM	-40 to 85	

- ⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).
- ⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.
- ⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.
- ⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.
- ⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.
- ⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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